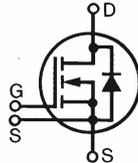
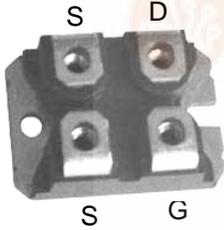


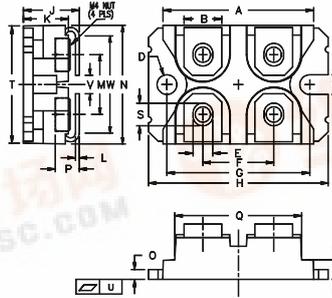
# SMOS44N50, SMOS48N50

## Power MOSFETs



G=Gate, D=Drain, S=Source

Dimensions SOT-227(ISOTOP)



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.20	1.489	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004
V	3.30	4.57	0.130	0.180
W	0.780	0.830	0.031	0.033

Symbol	Test Conditions	Maximum Ratings	Unit	
V <sub>DSS</sub>	T <sub>J</sub> =25°C to 150°C	500	V	
V <sub>DGR</sub>	T <sub>J</sub> =25°C to 150°C; R <sub>GS</sub> =1MΩ	500	V	
V <sub>GS</sub>	Continuous	±20	V	
V <sub>GSM</sub>	Transient	±30	V	
I <sub>D25</sub>	T <sub>C</sub> =25°C	44N50 48N50	44 48	A
I <sub>DM</sub>	T <sub>C</sub> =25°C; pulse width limited by T <sub>JM</sub>	44N50 48N50	176 192	A
I <sub>SM</sub>	T <sub>C</sub> =25°C		24	A
EAS	T <sub>C</sub> =25°C		30	mJ
dv/dt	I <sub>S</sub> ≤ I <sub>DM</sub> ; di/dt ≤ 100A/us; V <sub>DD</sub> ≤ V <sub>DSS</sub> T <sub>J</sub> ≤ 150°C; R <sub>G</sub> =2Ω	5	V/ns	
P <sub>D</sub>	T <sub>C</sub> =25°C	520	W	
T <sub>J</sub>		-55...+150	°C	
T <sub>JM</sub>		150	°C	
T <sub>stg</sub>		-55...+150	°C	
T <sub>L</sub>	1.6mm(0.063 in.) from case for 10s	-	°C	
V <sub>ISOL</sub>	50/60Hz,RMS t=1 min I <sub>ISOL</sub> ≤ 1mA t=1 s	2500 3000	V~	
M <sub>d</sub>	Mounting torque Terminal connection torque	1.5/13 1.5/13	Nm/lb.in.	
Weight		30	g	

